TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MP97FT, TC7MP97FK TC7MP98FT, TC7MP98FK

Low Voltage Triple Configurable Multiple Function Gate with 3.6 V Tolerant Inputs and Outputs

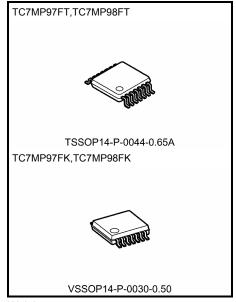
The TC7MP97,98 is a high performance CMOS multiple Function Gate which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6~\mathrm{V}.$

It independently consists of three circuits for Multiple Function Gate.

The output state is determined by seven patterns of 3-inputs. The user can choose the functions of Multiplexer, AND, OR, NAND, Schmitt Inverter, and Schmitt Buffer.

All inputs are equipped with protection circuits against static discharge.



Weight:

TSSOP14-P-0044-0.65A : 0.06 g(typ) VSSOP14-P-0030-0.50 : 0.02 g(typ)

Features

• Low-voltage operation :VCC = 1.2 to 3.6 V

• High-speed operation $: t_{pd} = 8.5 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V})$

 $: t_{pd} = 12.0 \text{ ns (max) (V}_{CC} = 2.3 \text{ to } 2.7 \text{ V})$

• Output current : $|IOH|/IOL = \pm 8 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

: $|IOH|/I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

: $|IOH|/I_{OL} = \pm 1.5 \text{ mA (min) (V}_{CC} = 1.65 \text{ V})$

• Latch-up performance : -300 mA

• ESD performance : Machine model $\geq \pm 200 \text{ V}$

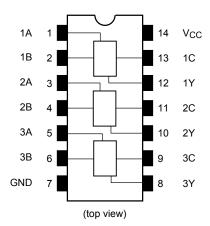
Human body model $\geq \pm 2000 \text{ V}$

Package : VSSOP14 (US14),TSSOP14

· Power-down protection is provided on all inputs and outputs



Pin Assignment (top view)



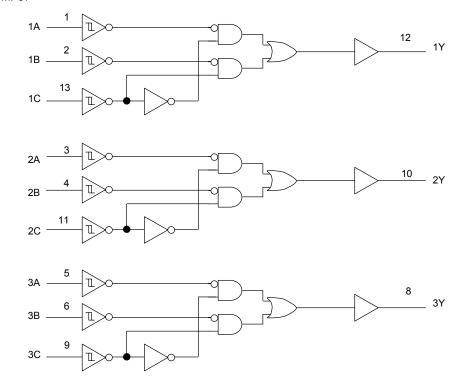
Truth Table

INPUTS			OUT	TPUT
	INPUIS		TC7MP97	TC7MP98
Α	В	С	Y	Υ
L	L	L	L	Н
L	L	Н	L	Н
L	Н	L	Н	L
L	Н	Н	L	Η
Н	L	L	L	Ι
Н	L	Н	Н	L
Н	Н	L	Н	L
Н	Н	Н	Н	L

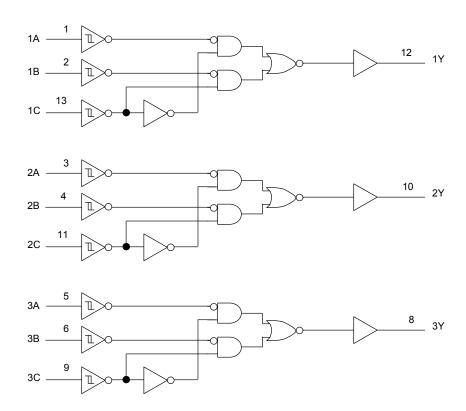


System Diagram

TC7MP97



TC7MP98



Logic configrations(1/2)

Function	Input Condition	TC7MP97 Logic symbol	TC7MP98 Logic symbol	FUNCTION TABLE
MP97 AND MP98 NAND	A=INPUT B=L-Level C=INPUT Y=OUTPUT	A Y	A Y	A B C Y 97 98 L L L L L H L L H H H L L L H
MP97 OR MP98 NOR	A=H-Level B=INPUT C=INPUT Y=OUTPUT	B Y	B Y	A B C Y 97 98 H L L L H H L H L H H L
MP97 Schmitt INV+NOR or Schmitt INV+AND MP98 Schmitt INV+OR or Schmitt INV+NAND	A=L-Level B=INPUT C=INPUT Y=OUTPUT	B OR OR C	B OR OR Y	A B C Y 97 98 L L L L H L H L H L H L H L H L H
MP97 Schmitt INV+NAND or Schmitt INV+OR MP98 Schmitt INV+AND or Schmitt INV+AND	A=INPUT B=H-Level C=INPUT Y=OUTPUT	A OF Y OR A C T Y	A OF Y OR C OR Y	A B C Y 97 98 L H L H L L H H L H H H L H L H H L H L
MP97 2 to 1 Selector MP98 2 to 1 Selector+INV	A=INPUT B=INPUT C=Select Y=OUTPUT	C A B Y	C A B Y	A B C Y 97 98 L L L L L H L H L H L H L H L H H H L H L



Logic configrations(2/2)

Function	Input Condition	TC7MP97	TC7MP98	FUNCTION TABLE
MP97 Schmitt INV MP98 Schmitt Buffer	A=L-Level B=H-Level C=INPUT Y=OUTPUT	CY	CY	A B C 97 98 L H L H L L H H L H
MP97 Schmitt Buffer MP98 Schmitt INV	A=H-Level B=L-Level C=INPUT Y=OUTPUT	C Y	C Y	A B C Y 97 98 H L L L H H L H H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=L-Level B=INPUT C=L-Level Y=OUTPUT	В Y	В Y	A B C 97 98 L L L L H L H L H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=H-Level B=INPUT C=L-Level Y=OUTPUT	В Y	В Y	A B C Y 97 98 H L L L H H H H L H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=INPUT B=L-Level C=H-Level Y=OUTPUT	A Y	A Y	A B C 97 98 L L H L H H L H H L



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	٧
DC output voltage	Vout	-0.5 to 4.6 (Note 2)	V
DC output voltage	VOU1	-0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20 (Note 4)	mA
DC output current	lout	±25	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±25	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: $V_{CC} = 0 V$

Note 3: High or Low state. IOUT absolute ratingmust be observed.

Note 4: Vout < GND, Vout > Vcc

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	1.2~3.6	V	
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	Vout	0~3.6 (Note 2)	V	
Output voltage	VOU1	0~V _{CC} (Note 3)		
		±8.0 (Note 4)		
Output current	I _{OH} /I _{OL}	±4.0 (Note 5)	mA	
		±1.5 (Note 6)		
Operating temperature	T _{opr}	-40~85	°C	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: $V_{CC} = 0 \text{ V}$

Note 3: High or low state

Note 4: V_{CC} = 3.0~3.6 V

Note 5: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 6: $V_{CC} = 1.65 \sim 1.8 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C)

Characteristics S		Symbol	Test C	ondition	V _{CC} (V)	Min	Max	Unit		
	1									
					1.2		1.10			
					1.4		1.20			
	H-level	VP	_	_	1.65		1.35	V		
					2.3		1.70			
					3.0		2.00			
Input voltage					3.6		2.20			
put voltago					1.2	0.10				
					1.4	0.20				
	L-level				1.65	0.30		V		
	L-level	V _N		_	2.3	0.50		V		
					3.0	0.70				
						0.80				
•					1.2	0.2	0.9			
			_		1.4	0.2	0.9	V		
					1.65	0.2	0.95			
Hysteresis voltage		V _H			2.3	0.3	1.0			
					3.0	0.3	1.2			
					3.6	0.3	1.2			
				$I_{OH} = -100 \mu A$	1.2~1.3	Vcc - 0.1	_			
				I _{OH} = -500 μA	1.4~1.6	Vcc - 0.2	_			
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -1.5 \text{ mA}$	1.65~1.95	Vcc - 0.3	_			
				$I_{OH} = -4.0 \text{ mA}$	2.3~2.7	Vcc - 0.4	_			
				$I_{OH} = -8.0 \text{ mA}$	3.0~3.6	2.40	_			
Output voltage				$I_{OL} = 100 \mu A$	1.2~1.3	_	0.10	V		
				I _{OL} = 500 μA	1.4~1.6	_	0.20			
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 3.0 mA	1.65~1.95	_	0.25			
			$I_{OL} = 4.0 \mathrm{r}$			I _{OL} = 4.0 mA	2.3~2.7	_	0.40	
				I _{OL} = 8.0 mA	3.0~3.6	_	0.40			
Input leakage current I _{IN} V _{IN} = 0-		V _{IN} = 0~3.6 V			_	±5.0	μΑ			
Power-off leakage of		loff	V _{IN} , V _{OUT} = 0~3.6	V	1.2~3.6	_	10.0	μA		
			$V_{IN} = V_{CC}$ or GND		1.2~3.6	_	20.0			
Quiescent supply cu	urrent	Icc	V _{CC} ≤ V _{IN} ≤ 3.6 V		1.2~3.6	_	±20.0	μΑ		
Increase in I _{CC} per	input	Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750			



AC Characteristics (Ta = -40 to 85° C, input: $t_r = t_f = 3.0$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
		Figure 4 Figure 2	1.8± 0.15	1.0	21.0	
	t _{pLH}	Figure 1, Figure 2 $CL = 10pF, R_1 = 1M \Omega$	2.5 ± 0.2	0.8	10.0	ns
Propagation delay time (A, B,C-Y)	t _{pHL}	CL = TOPF, RL = TWI 52	3.3 ± 0.3	0.6	7.0	
	t _{pLH} t _{pHL} t _{pLH} t _{pLH}	Figure 1, Figure 2 CL = 15pF, R_L = 1M Ω	1.8± 0.15	1.0	23.0	
			2.5 ± 0.2	0.8	11.0	ns
			3.3 ± 0.3	0.6	7.7	
		Figure 4 Figure 2	1.8± 0.15	1.0	27.0	
		Figure 1, Figure 2 $CL = 30pF$, $R_L = 1M \Omega$	2.5 ± 0.2	0.8	12.0	ns
		OL - Supr. RL - TIVI 22	3.3 ± 0.3	0.6	8.5	

Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 3.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
		V _{IH} = 1.8 V, V _{IL} = 0 V (Note	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 2.5 V, V _{IL} = 0 V (Note	2.5	0.6	V
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note	3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	1.8	-0.25	V
Quiet output minimum dynamic $V_{\mbox{OL}}$		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	3.3	-0.8	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	1.8	1.5	
		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test C	condition	V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	-	_	1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \; \text{MHz}$	(Note)	1.8, 2.5, 3.3	30	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit

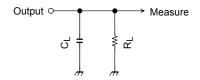
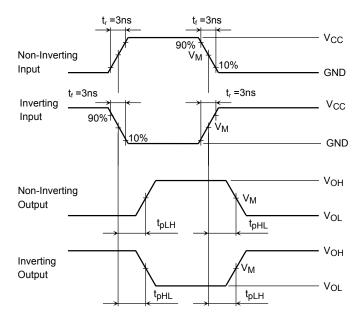


Figure 1

AC Waveform



Symbol		V _{CC}	
Syllibol	$3.3\pm0.3~\textrm{V}$	2.5 ± 0.2 V	1.8 V± 0.15 V
V _{IN}	V _{CC}	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2

Figure 2 t_{pLH}, t_{pHL}

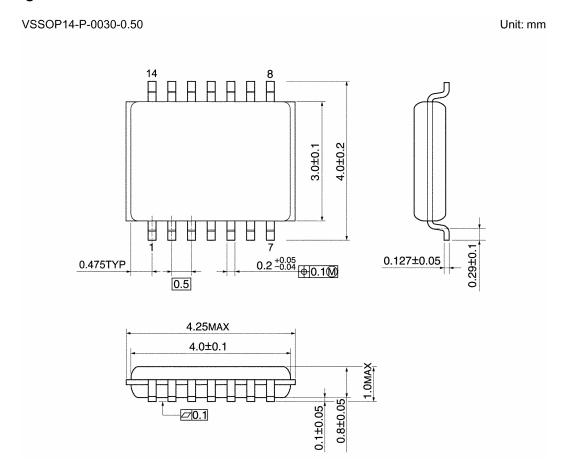
Package Dimensions

TSSOP14-P-0044-0.65A Unit: mm 6.4±0.2 $0.22^{+0.09}_{-0.06}$ 0.65 0.55TYP ||0.13M 5.4MAX 5.0±0.1 0~10 0.25 1.0±0.05 0.1±0.05 S Ø.1S (0.5)0.45~0.75

Weight: 0.06 g (typ.)



Package Dimensions



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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